

# Automotive 750 V, 800 A Dual Side Cooling Half-Bridge Power Module



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## VE-Trac™ Dual NVG800A75L4DSB

### Product Description

The NVG800A75L4DSB is part of a family of power modules with dual side cooling and compact footprints for Hybrid (HEV) and Electric Vehicle (EV) traction inverter application.

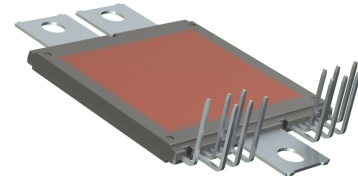
The module consists of two narrow mesa Field Stop (FS4) IGBTs in a half-bridge configuration. The chipset utilizes the new narrow mesa IGBT technology in providing high current density and robust short circuit protection with higher blocking voltage to deliver outstanding performance in EV traction applications.

### Features

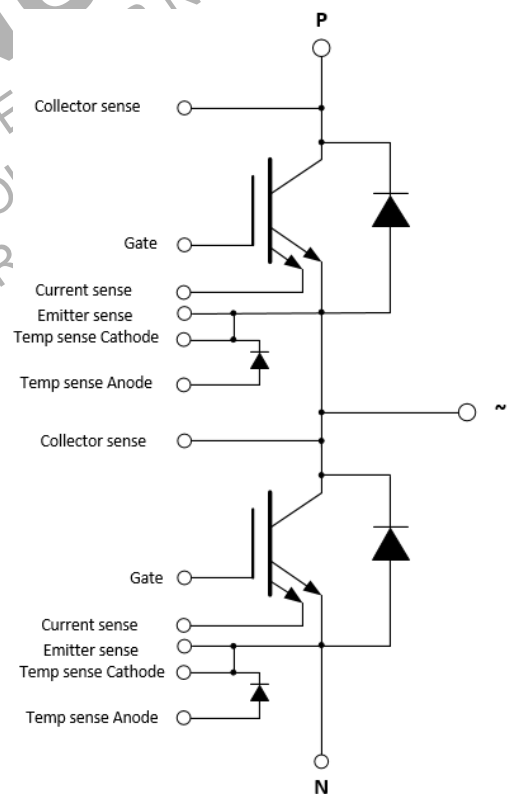
- Dual-Side Cooling
- Integrated Chip Level Temperature and Current Sensor
- $T_{vj \text{ max}} = 175^{\circ}\text{C}$  for Continuous Operation
- Ultra-low Stray Inductance
- Low  $V_{CESAT}$  and Switching Losses
- Automotive Grade FS4 IGBT & Soft Diode Chip Technologies
- 4.2 kV Isolated DBC Substrate
- This Device is RoHS Compliant

### Typical Applications

- Hybrid and Electric Vehicle Traction Inverter
- High Power DC-DC Converter



AHPM15-CEC  
CASE 100DV



### ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

# VE-Trac™ Dual NVG800A75L4DSB

## PIN DESCRIPTION

Pin #	Pin	Pin Function Description	Pin Arrangement
1	N	Low Side Emitter	
2	P	High Side Collector	
3	H/S COLLECTOR SENSE	High Side Collector Sense	
4	H/S CURRENT SENSE	High Side Current Sense	
5	H/S EMITTER SENSE	High Side Emitter Sense	
6	H/S GATE	High Side Gate	
7	H/S TEMP SENSE (CATHODE)	High Side Temp sense Diode Cathode	
8	H/S TEMP SENSE (ANODE)	High Side Temp sense Diode Anode	
9	~	Phase Output	
10	L/S CURRENT SENSE	Low Side Current Sense	
11	L/S EMITTER SENSE	Low Side Emitter Sense	
12	L/S GATE	Low Side Gate	
13	L/S TEMP SENSE (CATHODE)	Low Side Temp sense Diode Cathode	
14	L/S TEMP SENSE (ANODE)	Low Side Temp sense Diode Anode	
15	L/S COLLECTOR SENSE	Low Side Collector Sense	

## Materials

DBC Substrate: Al<sub>2</sub>O<sub>3</sub> isolated substrate, basic isolation, and copper on both sides

Lead Frame: Copper with Tin electro-plating

## Flammability Information

All materials present in the power module meet UL flammability rating class 94V-0

## MODULE CHARACTERISTICS

Symbol	Parameter	Rating	Unit		
T <sub>vj</sub>	Continuous Operating Junction Temperature Range	-40 to 175	°C		
T <sub>STG</sub>	Storage Temperature Range	-40 to 125	°C		
V <sub>ISO</sub>	Isolation Voltage, DC, t = 1 s	4200	V		
Creepage	Terminal to Terminal	6.0	mm		
Clearance	Terminal to Terminal	3.2	mm		
CTI	Comparative Tracking Index	>600	-		
		<b>Min</b>	<b>Typ</b>	<b>Max</b>	
L <sub>sCE</sub>	Stray Inductance		8		nH
R <sub>CC+EE'</sub>	Module Lead Resistance, Terminals - Chip		0.15		mΩ
G	Module Weight		75		g
M	M4 Screws for Module Terminals			2.2	Nm

# VE-Trac™ Dual NVG800A75L4DSB

## ABSOLUTE MAXIMUM RATINGS (T<sub>VJ</sub> = 25°C, Unless Otherwise Specified)

Symbol	Parameter	Rating	Unit
<b>IGBT</b>			
V <sub>CES</sub>	Collector to Emitter Voltage	750	V
V <sub>GES</sub>	Gate to Emitter Voltage	±20	V
I <sub>CN</sub>	Implemented Collector Current	800	A
I <sub>C nom</sub>	Continuous DC Collector Current, T <sub>VJmax</sub> = 175°C, T <sub>F</sub> = 65°C, Ref. Heatsink	550 (Note 1)	A
I <sub>CRM</sub>	Pulsed Collector Current @ V <sub>GE</sub> = 15 V, t <sub>p</sub> = 1 ms	1600	A

## DIODE

V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	750	V
I <sub>FN</sub>	Implemented Forward Current	800	A
I <sub>F</sub>	Continuous Forward Current, T <sub>VJmax</sub> = 175°C, T <sub>F</sub> = 65°C, Ref. Heatsink	420 (Note 1)	A
I <sub>FRM</sub>	Repetitive Peak Forward Current, t <sub>p</sub> = 1 ms	1600	A
I <sup>2</sup> t value	V <sub>R</sub> = 0 V, t <sub>p</sub> = 10 ms, T <sub>VJ</sub> = 150°C T <sub>VJ</sub> = 175°C	20000 18000	A <sup>2</sup> s

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Verified by characterization, not by test.

## THERMAL CHARACTERISTICS (Verified by characterization, not by test.)

Symbol	Parameter	Min	Typ	Max	Unit
IGBT.R <sub>th,J-C</sub>	Effective R <sub>th</sub> , Junction to Case (Note 2)		0.05	0.07	°C/W
IGBT.R <sub>th,J-F</sub>	Effective R <sub>th</sub> , Junction to Fluid, λ <sub>TJM</sub> = 6 W/m-K, F = 660 N 10 L/min, 65°C, 50/50 EGW, Ref. Heatsink		0.14		°C/W
Diode.R <sub>th,J-C</sub>	Effective R <sub>th</sub> , Junction to Case (Note 2)		0.08	0.10	°C/W
Diode.R <sub>th,J-F</sub>	Effective R <sub>th</sub> , Junction to Fluid, λ <sub>TJM</sub> = 6 W/m-K, F = 660 N 10 L/min, 65°C, 50/50 EGW, Ref. Heatsink		0.21		°C/W

2. For the measurement point of case temperature (T<sub>c</sub>), DBC discoloration, picker circle print is allowed, please refer to the VE-Trac Dual assembly guide for additional details about acceptable DBC surface finish.

# VE-Trac™ Dual NVG800A75L4DSB

## CHARACTERISTICS OF IGBT (T<sub>vj</sub> = 25°C, Unless Otherwise Specified)

Parameters	Conditions	Min	Typ	Max	Unit
V <sub>CESAT</sub>	Collector to Emitter Saturation Voltage (Terminal) V <sub>GE</sub> = 15 V, I <sub>C</sub> = 600 A, T <sub>vj</sub> = 25°C T <sub>vj</sub> = 150°C T <sub>vj</sub> = 175°C V <sub>GE</sub> = 15 V, I <sub>C</sub> = 800 A, T <sub>vj</sub> = 25°C T <sub>vj</sub> = 150°C T <sub>vj</sub> = 175°C	- - - - - -	1.30 1.42 1.45 1.44 1.64 1.68	1.55 - - - - -	V
I <sub>CES</sub>	Collector to Emitter Leakage Current V <sub>GE</sub> = 0, V <sub>CE</sub> = 750 V T <sub>vj</sub> = 25°C T <sub>vj</sub> = 175°C	- -	- 8	1 -	mA
I <sub>GES</sub>	Gate – Emitter Leakage Current V <sub>CE</sub> = 0, V <sub>GE</sub> = ±20 V	-	-	±400	nA
V <sub>th</sub>	Threshold Voltage V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 500 mA	4.6	5.5	6.2	V
Q <sub>G</sub>	Total Gate Charge V <sub>GE</sub> = -8 to 15 V, V <sub>CE</sub> = 400 V	-	2.2	-	μC
R <sub>Gint</sub>	Internal Gate Resistance	-	2	-	Ω
C <sub>ies</sub>	Input Capacitance V <sub>CE</sub> = 30 V, V <sub>GE</sub> = 0 V, f = 1 MHz	-	48	-	nF
C <sub>oes</sub>	Output Capacitance V <sub>CE</sub> = 30 V, V <sub>GE</sub> = 0 V, f = 1 MHz	-	1.37	-	nF
C <sub>res</sub>	Reverse Transfer Capacitance V <sub>CE</sub> = 30 V, V <sub>GE</sub> = 0 V, f = 1 MHz	-	0.15	-	nF
T <sub>d,on</sub>	Turn On Delay, Inductive Load I <sub>C</sub> = 600 A, V <sub>CE</sub> = 400 V V <sub>GE</sub> = +15/-8 V R <sub>g,on</sub> = 4.7 Ω T <sub>vj</sub> = 25°C T <sub>vj</sub> = 150°C T <sub>vj</sub> = 175°C	- - - -	253 282 287	- - -	ns
T <sub>r</sub>	Rise Time, Inductive Load I <sub>C</sub> = 600 A, V <sub>CE</sub> = 400 V V <sub>GE</sub> = +15/-8 V R <sub>g,on</sub> = 4.7 Ω T <sub>vj</sub> = 25°C T <sub>vj</sub> = 150°C T <sub>vj</sub> = 175°C	- - - -	94 112 117	- - -	ns
T <sub>d,off</sub>	Turn Off Delay, Inductive Load I <sub>C</sub> = 600 A, V <sub>CE</sub> = 400 V V <sub>GE</sub> = +15/-8 V R <sub>g,off</sub> = 15 Ω T <sub>vj</sub> = 25°C T <sub>vj</sub> = 150°C T <sub>vj</sub> = 175°C	- - - -	760 790 800	- - -	ns
T <sub>f</sub>	Fall Time, Inductive Load I <sub>C</sub> = 600 A, V <sub>CE</sub> = 400 V V <sub>GE</sub> = +15/-8 V R <sub>g,off</sub> = 15 Ω T <sub>vj</sub> = 25°C T <sub>vj</sub> = 150°C T <sub>vj</sub> = 175°C	- - - -	95 140 153	- - -	ns
E <sub>ON</sub>	Turn-On Switching Loss (including diode reverse recovery loss) I <sub>C</sub> = 600 A, V <sub>CE</sub> = 400 V, V <sub>GE</sub> = +15/-8 V, L <sub>s</sub> = 20 nH, R <sub>g,on</sub> = 4.7 Ω di/dt (T <sub>vj</sub> = 25°C) = 5.13 A/ns di/dt (T <sub>vj</sub> = 175°C) = 4.11 A/ns T <sub>vj</sub> = 25°C T <sub>vj</sub> = 150°C T <sub>vj</sub> = 175°C	- - -	21.30 32.55 33.66	- - -	mJ
E <sub>OFF</sub>	Turn-Off Switching Loss I <sub>C</sub> = 600 A, V <sub>CE</sub> = 400 V, V <sub>GE</sub> = +15/-8 V, L <sub>s</sub> = 20 nH, R <sub>g,off</sub> = 15 Ω dv/dt (T <sub>vj</sub> = 25°C) = 2.81 V/ns dv/dt (T <sub>vj</sub> = 175°C) = 2.11 V/ns T <sub>vj</sub> = 25°C T <sub>vj</sub> = 150°C T <sub>vj</sub> = 175°C	- - -	22.62 31.77 33.60	- - -	mJ
E <sub>SC</sub>	Minimum Short Circuit Energy Withstand V <sub>GE</sub> = 15 V, V <sub>CC</sub> = 400 V T <sub>vj</sub> = 25°C T <sub>vj</sub> = 175°C	5 7.5	- -	- -	J

# VE-Trac™ Dual NVG800A75L4DSB

## CHARACTERISTICS OF INVERSE DIODE (T<sub>VJ</sub> = 25°C, Unless Otherwise Specified)

Parameters		Conditions	Min	Typ	Max	Unit	
V <sub>F</sub>	Diode Forward Voltage (Terminal)	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 600 A,	T <sub>VJ</sub> = 25°C	-	1.50	1.70	V
			T <sub>VJ</sub> = 150°C	-	1.46	-	
			T <sub>VJ</sub> = 175°C	-	1.44	-	
		V <sub>GE</sub> = 0 V, I <sub>C</sub> = 800 A,	T <sub>VJ</sub> = 25°C	-	1.73	-	
			T <sub>VJ</sub> = 150°C	-	1.69	-	
			T <sub>VJ</sub> = 175°C	-	1.68	-	
E <sub>rr</sub>	Reverse Recovery Energy	I <sub>F</sub> = 600 A, V <sub>R</sub> = 400 V, V <sub>GE</sub> = -8 V, R <sub>g,on</sub> = 4.7 Ω, -di/dt = 3.12 A/ns (175°C)	T <sub>VJ</sub> = 25°C	-	3.58	-	mJ
			T <sub>VJ</sub> = 150°C	-	11.71	-	
			T <sub>VJ</sub> = 175°C	-	12.33	-	
Q <sub>RR</sub>	Recovered Charge	I <sub>F</sub> = 600 A, V <sub>R</sub> = 400 V, V <sub>GE</sub> = -8 V, R <sub>g,on</sub> = 4.7 Ω, -di/dt = 3.12 A/ns (175°C)	T <sub>VJ</sub> = 25°C	-	16.36	-	μC
			T <sub>VJ</sub> = 150°C	-	47.65	-	
			T <sub>VJ</sub> = 175°C	-	49.78	-	
I <sub>rr</sub>	Peak Reverse Recovery Current	I <sub>F</sub> = 600 A, V <sub>R</sub> = 400 V, V <sub>GE</sub> = -8 V, R <sub>g,on</sub> = 4.7 Ω, -di/dt = 3.12 A/ns (175°C)	T <sub>VJ</sub> = 25°C	-	220	-	A
			T <sub>VJ</sub> = 150°C	-	350	-	
			T <sub>VJ</sub> = 175°C	-	360	-	

## SENSOR CHARACTERISTICS (T<sub>VJ</sub> = 25°C, Unless Otherwise Specified)

Parameters		Conditions	Min	Typ	Max	Unit	
T <sub>sense</sub>	Temperature Sense	I <sub>F</sub> = 1 mA,	T <sub>VJ</sub> = -40°C	-	2.96	-	V
			T <sub>VJ</sub> = 25°C	2.46 (Note 3)	2.54	2.60 (Note 3)	
			T <sub>VJ</sub> = 150°C	-	1.76	-	
			T <sub>VJ</sub> = 175°C	-	1.61	-	
I <sub>sense</sub>	Current Sense	R <sub>shunt</sub> = 5 Ω	I <sub>C</sub> = 1600 A	-	379	-	mV
			I <sub>C</sub> = 800 A	-	200	-	
			I <sub>C</sub> = 100 A	-	43.0	-	
		R <sub>shunt</sub> = 20 Ω	I <sub>C</sub> = 1600 A	-	644	-	
			I <sub>C</sub> = 800 A	-	351	-	
			I <sub>C</sub> = 100 A	-	94.0	-	

3. Measured at chip level

IGBT Output Characteristic

$V_{GE} = +15V$

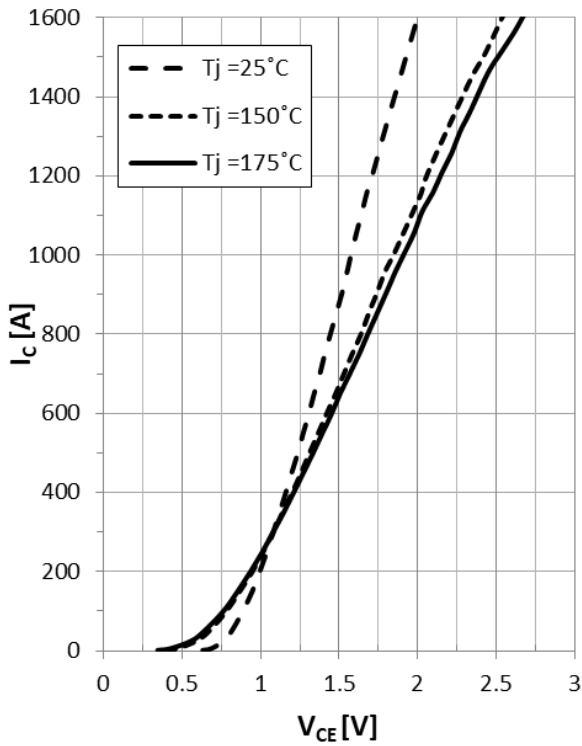


Figure 1. IGBT Output Characteristic

IGBT Transfer Characteristic

$V_{CE} = 20V$

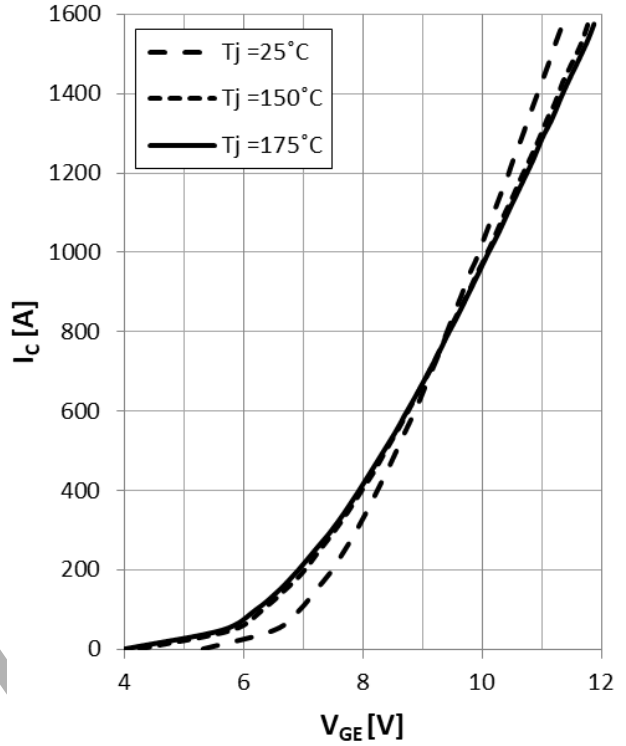


Figure 2. IGBT Transfer Characteristic

IGBT Output Characteristic

$T_j = +25^\circ C$

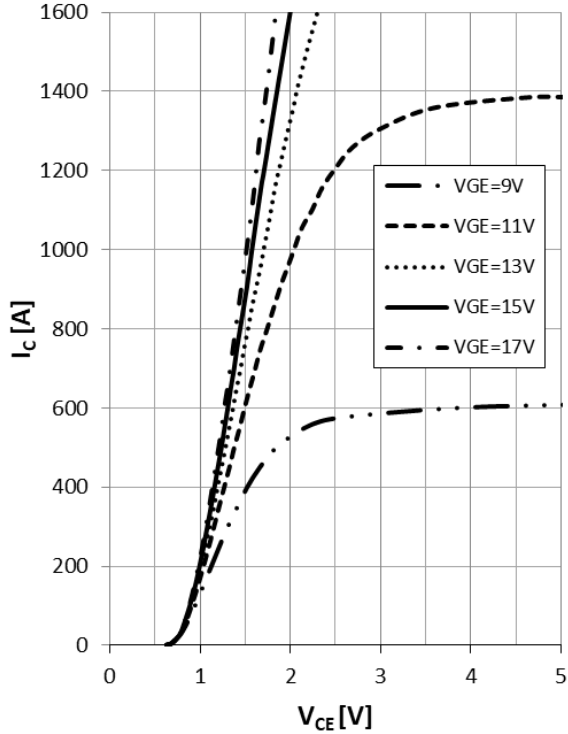


Figure 3. IGBT Output Characteristic

IGBT Output Characteristic

$T_j = +175^\circ C$

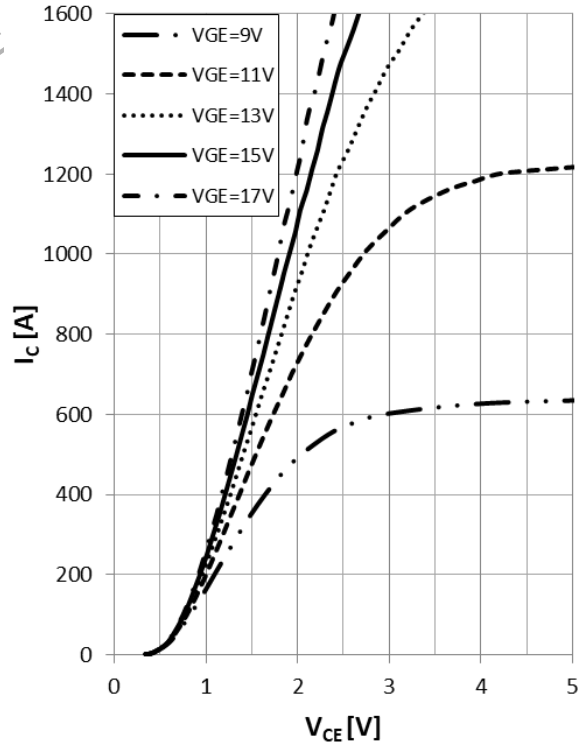


Figure 4. IGBT Output Characteristic

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## Gate Charge Characteristic

$V_{CE} = 400V, I_C = 600A, T_{vj} = 25^\circ C$

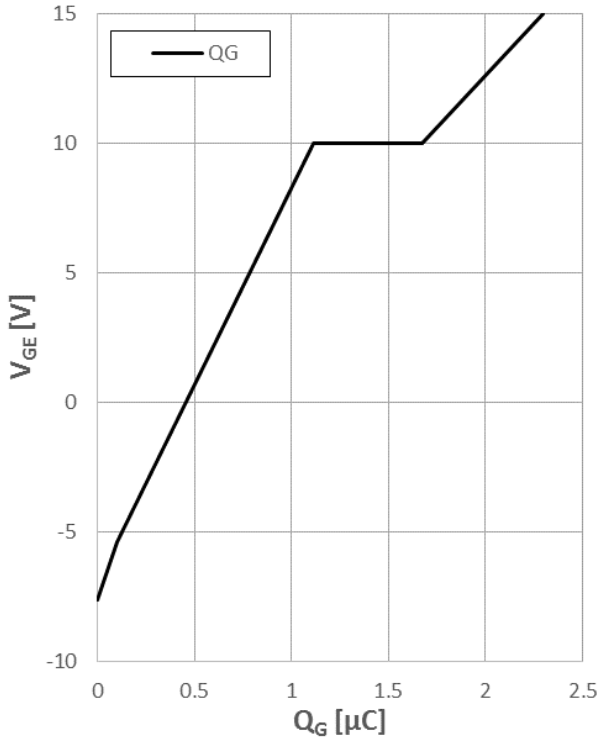


Figure 5. Gate Charge Characteristic

## Capacitance Characteristic

$V_{GE} = 0V, T_{vj} = 25^\circ C, f = 1MHz$

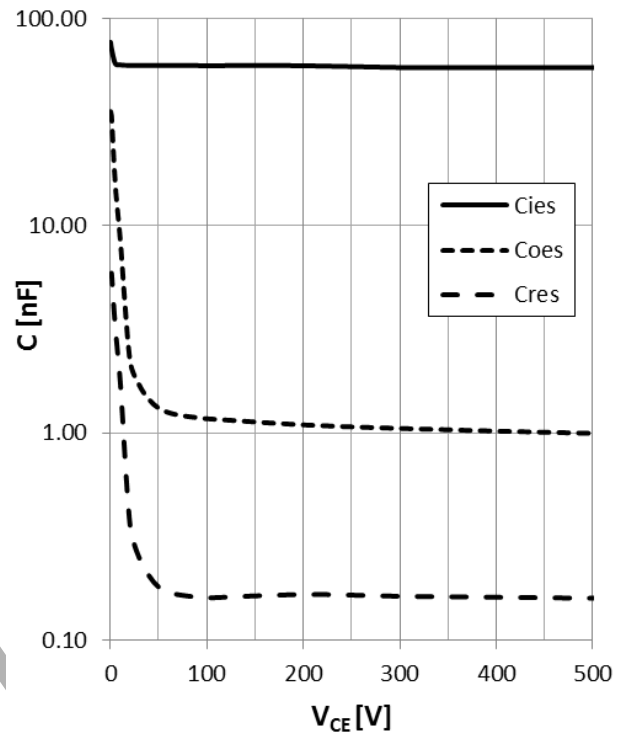


Figure 6. Capacitance Characteristic

## $E_{ON}$ vs $I_C$

$V_{GE} = +15/-8V, R_{Gon} = 4.7\Omega, R_{Goff} = 15\Omega, V_{CE} = 400V$

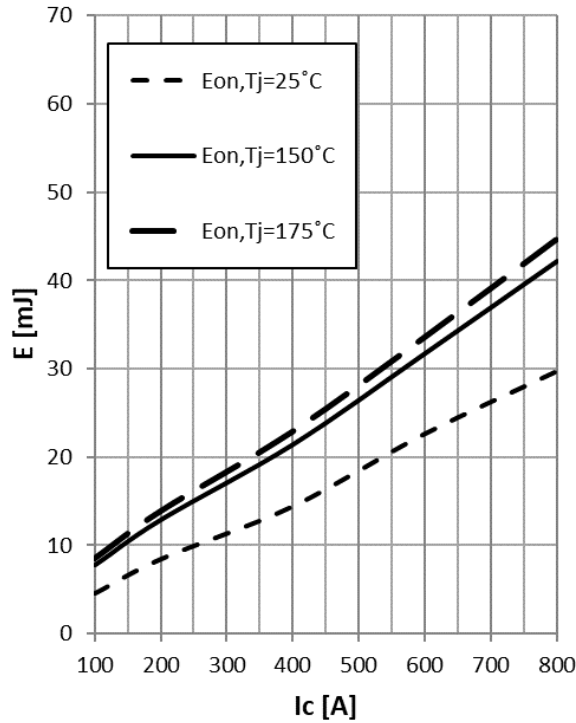


Figure 7.  $E_{ON}$  vs.  $I_C$

## $E_{ON}$ vs $R_g$

$V_{GE} = +15/-8V, I_C = 600A, V_{CE} = 400V$

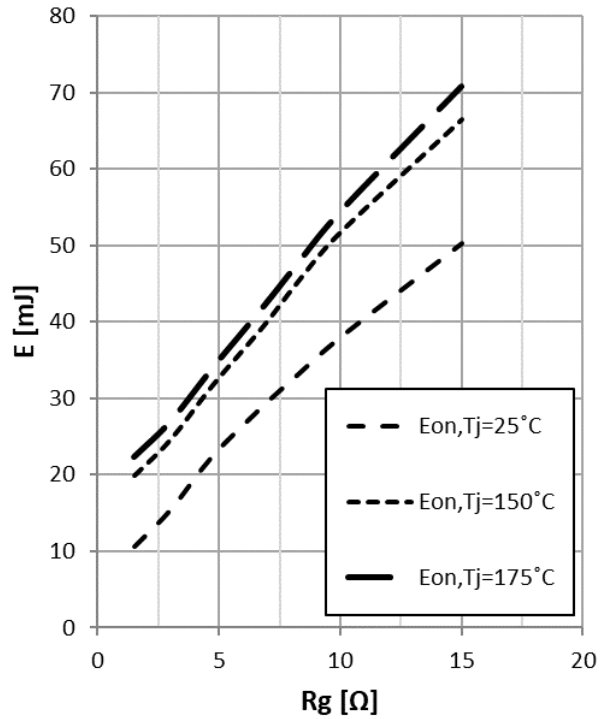


Figure 8.  $E_{ON}$  vs.  $R_g$

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## E<sub>OFF</sub> vs I<sub>c</sub>

V<sub>GE</sub>=+15/-8V, R<sub>Gon</sub>= 4.7Ω, R<sub>Goff</sub>= 15Ω, V<sub>CE</sub>=400V

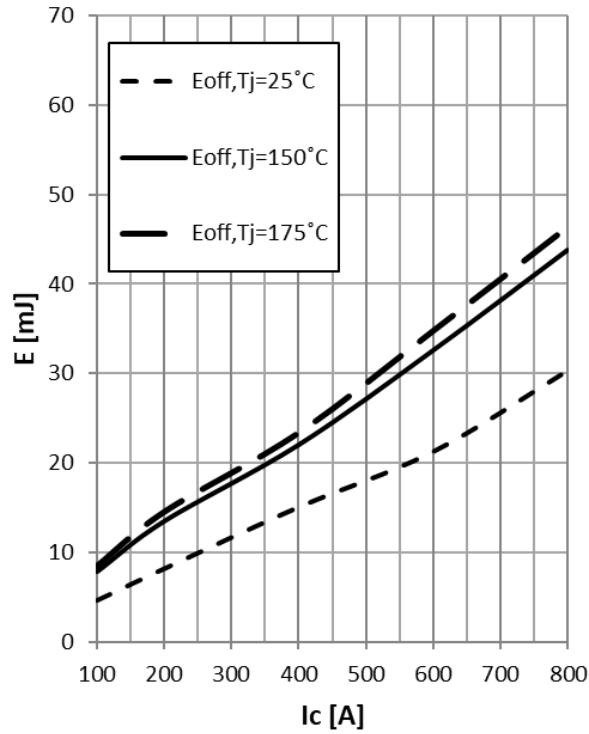


Figure 9. E<sub>OFF</sub> vs. I<sub>c</sub>

## E<sub>OFF</sub> vs R<sub>g</sub>

V<sub>GE</sub> = +15/-8V, I<sub>c</sub>=600A V<sub>CE</sub>=400V

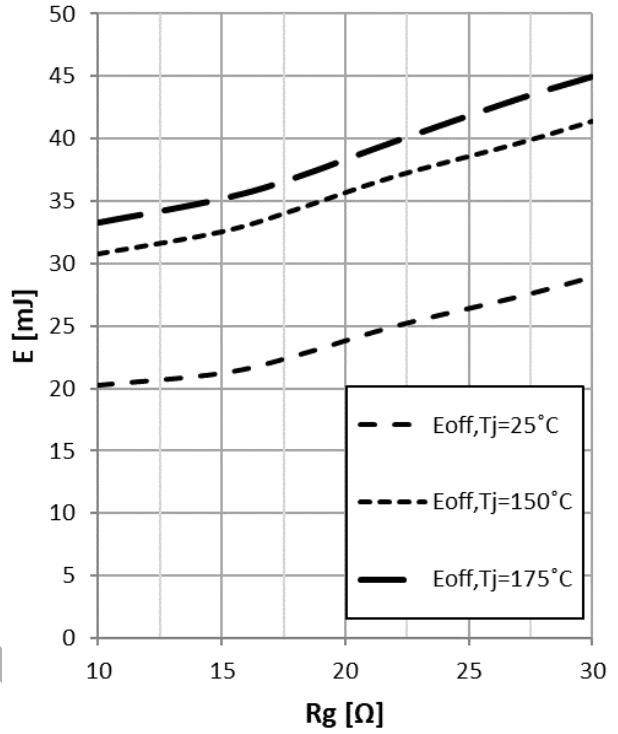


Figure 10. E<sub>OFF</sub> vs. R<sub>g</sub>

## IGBT Switching Times vs I<sub>c</sub>, T<sub>vj</sub> = 25°C

V<sub>GE</sub>=+15/-8V, R<sub>Gon</sub>= 4.7Ω, R<sub>Goff</sub>= 15Ω, V<sub>CE</sub>=400V

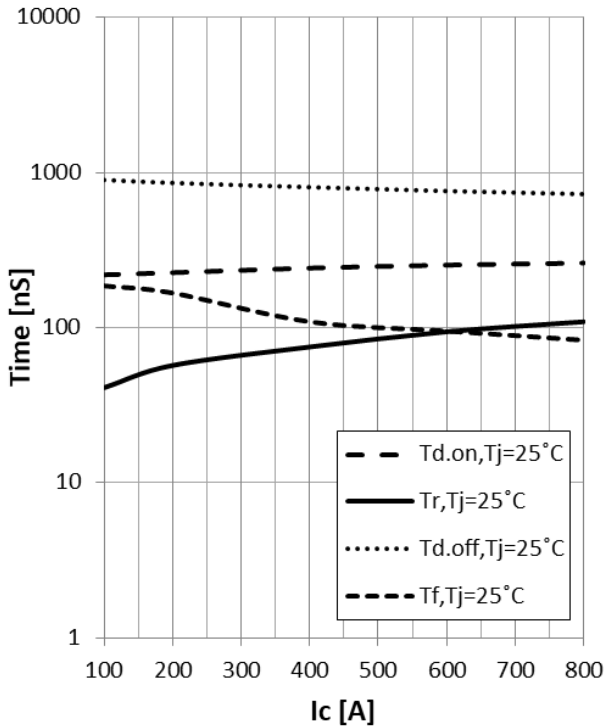


Figure 11. IGBT Switching Times vs I<sub>c</sub>, T<sub>vj</sub> = 25°C

## IGBT Switching Times vs I<sub>c</sub>, T<sub>vj</sub> = 175°C

V<sub>GE</sub>=+15/-8V, R<sub>Gon</sub>= 4.7Ω, R<sub>Goff</sub>= 15Ω, V<sub>CE</sub>=400V

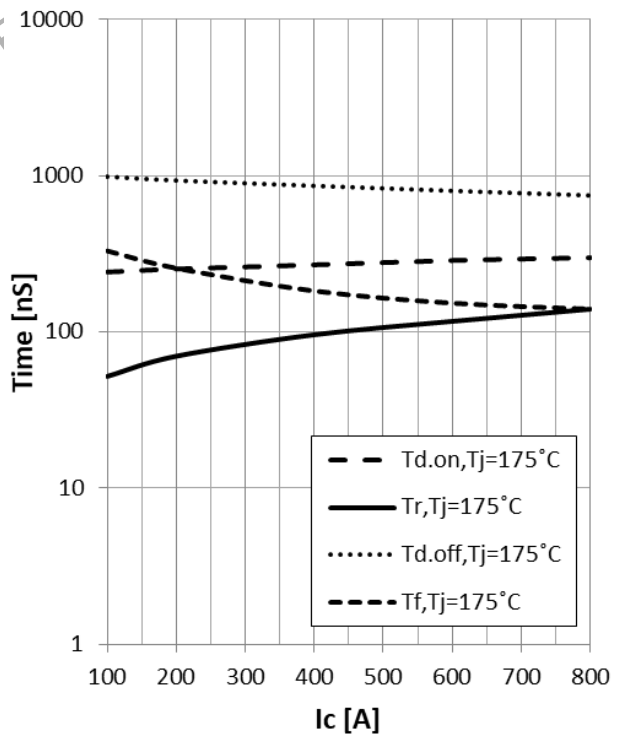


Figure 12. IGBT Switching Times vs I<sub>c</sub>, T<sub>vj</sub> = 175°C



**Reverse Bias Safe Operating Area**

$V_{GE} = +15/-8V$ ,  $R_{Goff} = 15\Omega$ ,  $T_{vj} = 175^{\circ}C$

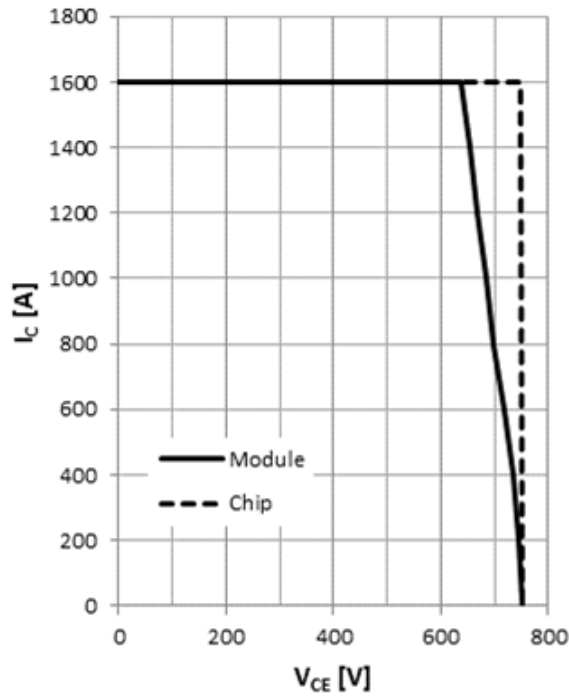


Figure 13. Reverse Bias Safe Operating Area

**IGBT Transient Thermal Impedance (typ)**

10L/min,  $T_f = 65^{\circ}C$ , 50/50 EGW, Ref. Heatsink

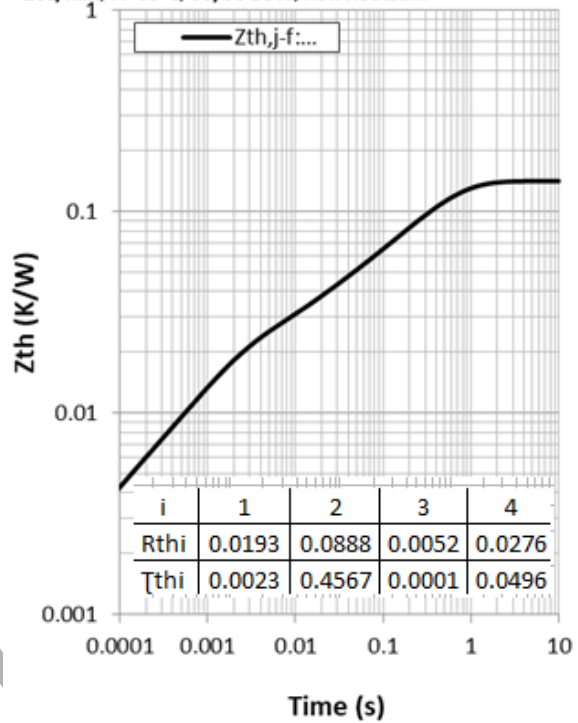


Figure 14. IGBT Transient Thermal Impedance

**Diode Forward Characteristic**

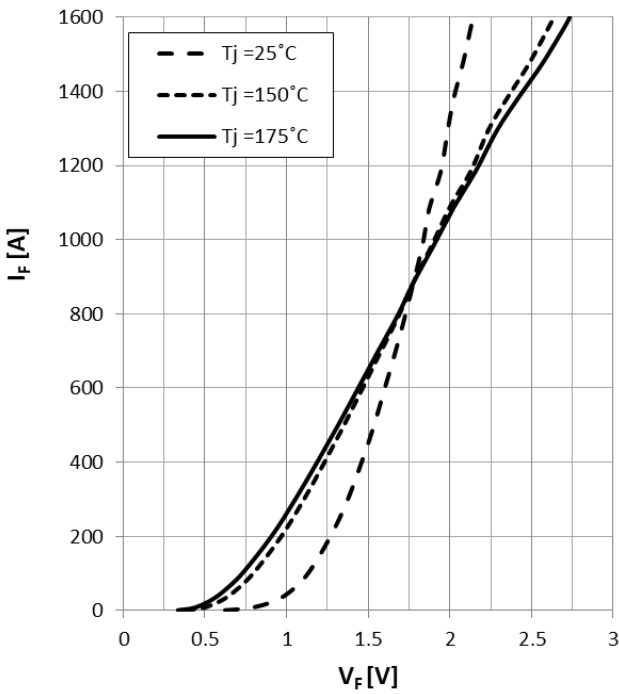


Figure 15. Diode Forward Characteristic

**Diode Switching losses vs  $I_F$**

$R_{Gon} = 4.7\Omega$ ,  $V_{CE} = 400V$

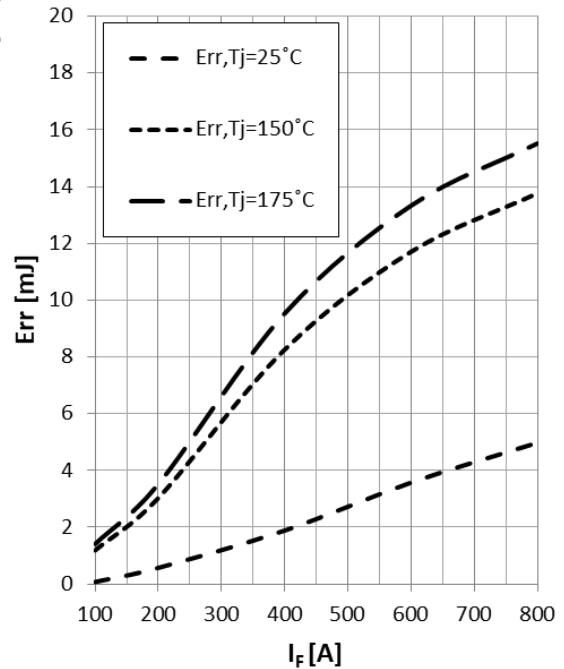


Figure 16. Diode Switching Losses vs.  $I_F$

Diode Switching losses vs Rg

I<sub>F</sub>=600A, V<sub>CE</sub>=400V

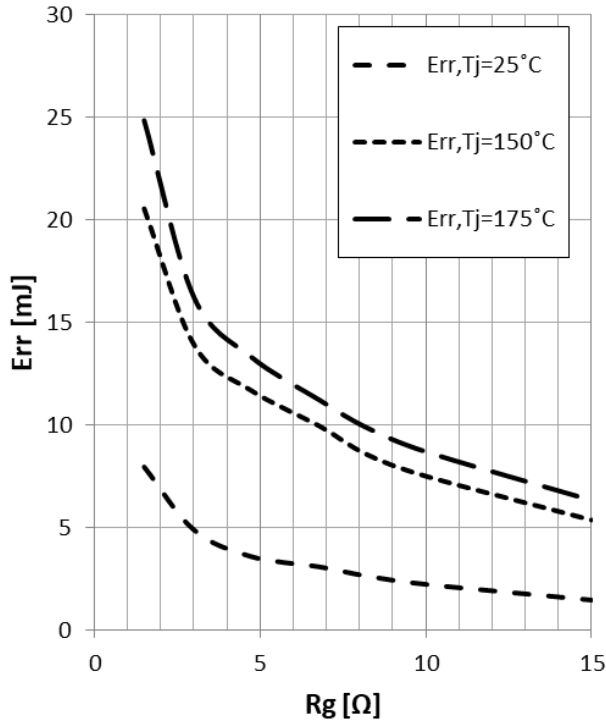


Figure 17. Diode Switching Losses vs. Rg

Diode Transient Thermal Impedance (typ)

10L/min, T<sub>f</sub>=65°C, 50/50 EGW, Ref. Heatsink

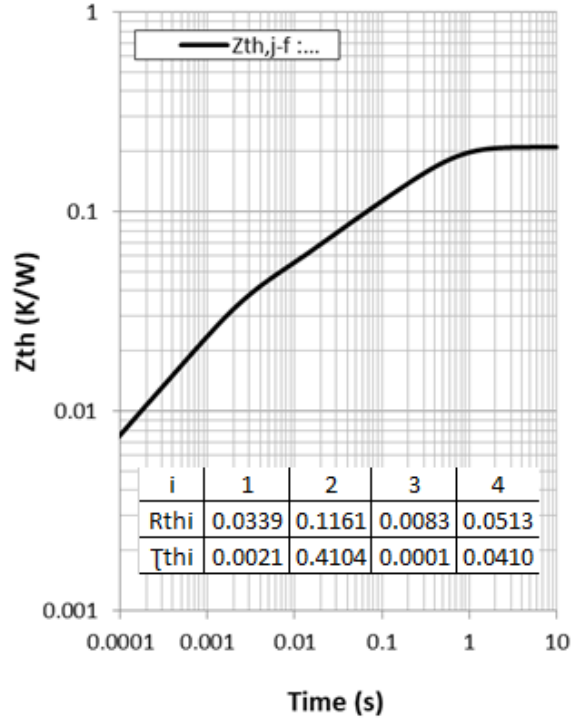


Figure 18. Diode Transient Thermal Impedance

Temperature Sensor Characteristic

I<sub>bias</sub> = 1mA

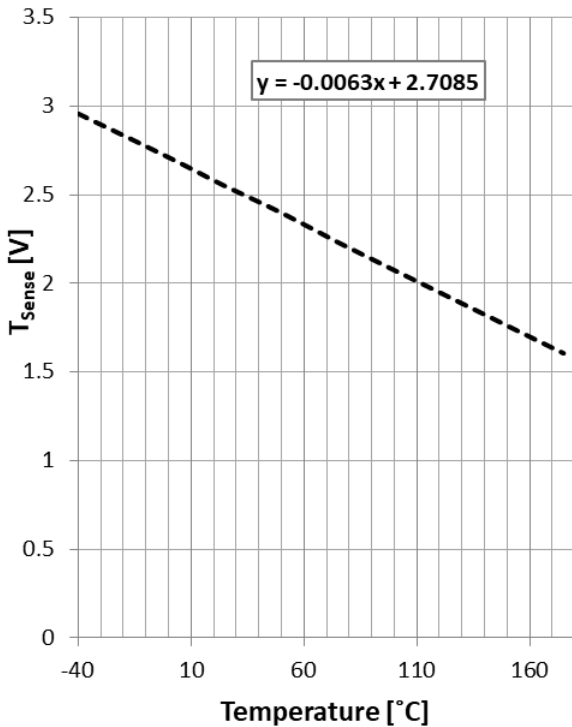


Figure 19. Temperature Sensor Characteristic

Current Sensor Characteristic

R<sub>shunt</sub> = 5 Ω

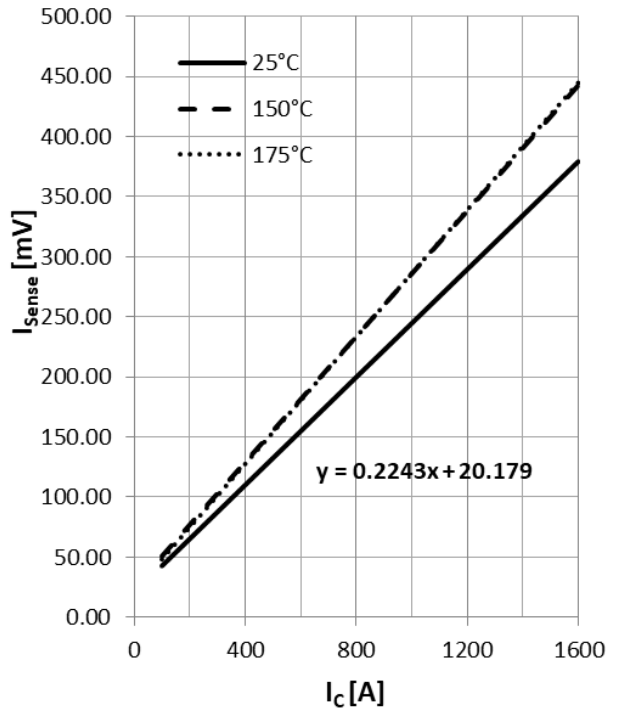


Figure 20. Current Sensor Characteristic

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## Current Sensor Characteristic

$R_{shunt} = 20 \Omega$

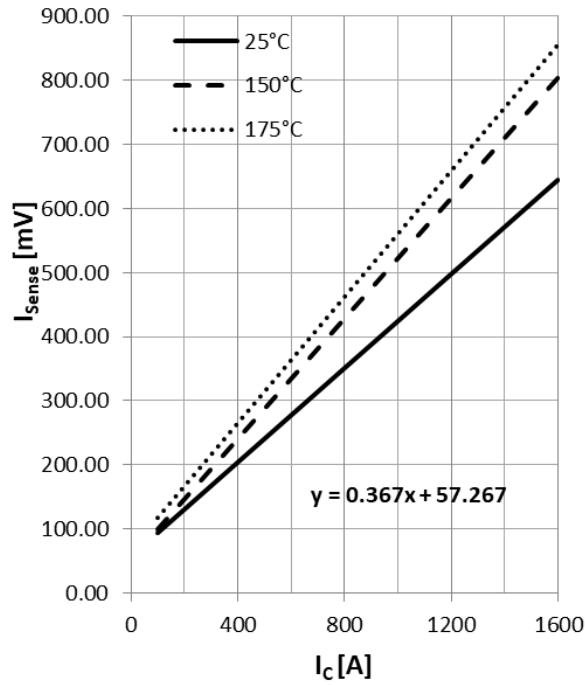


Figure 21. Current Sensor Characteristic

## Maximum allowed Vce

$I_{CES} = 1mA, T_{vj} \leq 25^\circ C; I_{CES} = 30mA, T_{vj} > 25^\circ C$

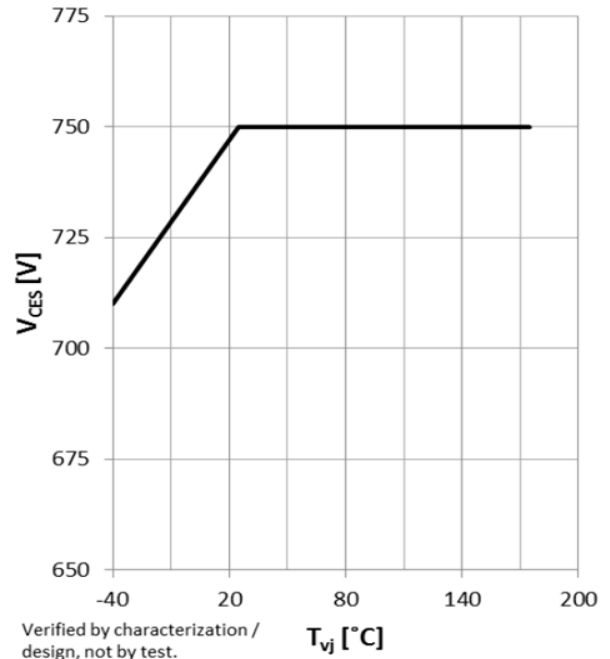


Figure 22. Maximum Allowed  $V_{CE}$

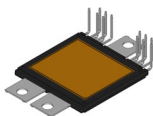
DISCONTINUED

THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN. PLEASE CONTACT YOUR ONSEMI REPRESENTATIVE FOR INFORMATION.

## ORDERING INFORMATION

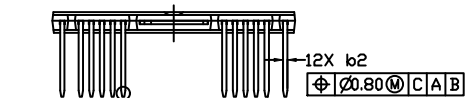
Part Number	Device Marking	Package	Shipping
NVG800A75L4DSB	N875DSB	AHPM15-CEC	6 Units / Tube

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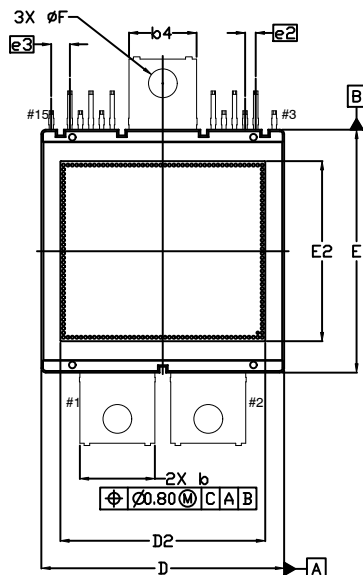


AHPM15-CEC  
CASE 100DV  
ISSUE A

DATE 03 OCT 2022



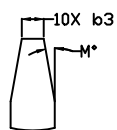
END VIEW



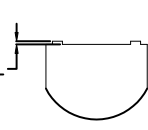
TOP VIEW



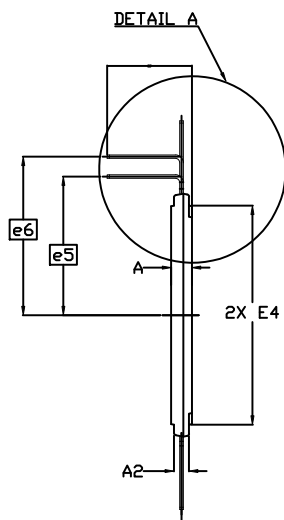
END VIEW



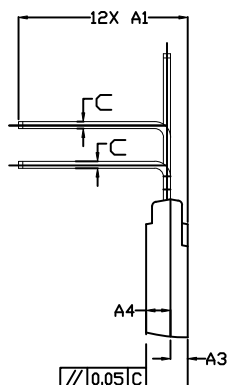
DETAIL B



DETAIL C

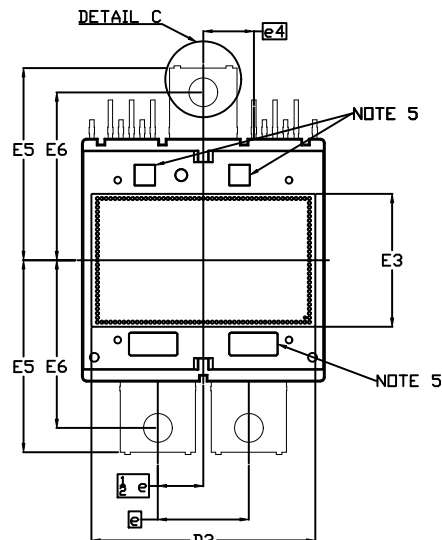


SIDE VIEW



DETAIL A

- NOTES:  
1. DIMENSIONING AND TOLERANCING PER. ASME Y14.5M, 2009.  
2. CONTROLLING DIMENSION: MILLIMETERS  
3. DIMENSIONS D & E DO NOT INCLUDE MOLD PROTRUSIONS  
4. DIMENSIONS b, b2 DO NOT INCLUDE DAMBAR REMAIN.  
5. MARKING AREA.



BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.65	4.70	4.75
A1	18.82	19.17	19.52
A2	3.20	3.40	3.60
A3	1.95 REF		
A4	2.75 REF		
b	16.90	17.00	17.10
b2	0.90	1.00	1.10
b3	0.50 REF		
b4	15.20	15.30	15.40
c	0.70	0.80	0.90
D	54.80	55.00	55.20
D2	46.20	46.50	46.80
D3	50.70	51.00	51.30
E	54.80	55.00	55.20

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E2	40.50	40.80	41.10
E3	29.80	30.10	30.40
E4	49.40	49.60	49.80
E5	43.35	43.70	44.05
E6	37.70	38.00	38.30
e	20.60 BSC		
e2	2.40 BSC		
e3	4.20 BSC		
e4	11.45 BSC		
e5	31.40 BSC		
e6	35.90 BSC		
F	6.45	6.50	6.55
L	0.50 REF		
M	10* REF		

GENERIC  
MARKING DIAGRAM\*



ZZZ = Assembly Lot Code  
AT = Assembly & Test Site Code  
YWW = Year and Work Week Code  
XXXXXX = Specific Device Code  
NNNNN = Serial Number

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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